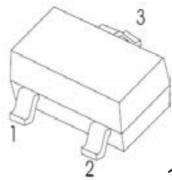




FEATURES

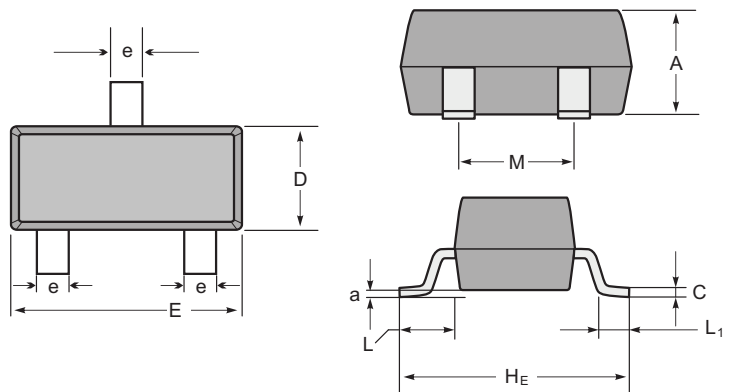
- Complimentary to SS8550



1.BASE
2.EMITTER
3.COLLECTOR

Marking

Type number	Marking code
SS8050	Y1



SOT-23 mechanical data

UNIT		A	C	D	E	HE	e	M	L	L ₁	a
mm	max	1.1	0.15	1.4	3.0	2.6	0.5	1.95	0.55 (ref)	0.36 (ref)	0.0
	min	0.9	0.08	1.2	2.8	2.2	0.3	1.7			0.15
mil	max	43	6	55	118	102	20	77	22 (ref)	14 (ref)	0.0
	min	35	3	47	110	87	12	67			6

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector–Base Voltage	V_{CBO}	40	V
Collector–Emitter Voltage	V_{CEO}	25	V
Emitter–Base Voltage	V_{EBO}	5	V
Collector Current — Continuous	I_C	1.5	A
Collector Power Dissipation	P_C	300	mW
Thermal Resistance From Junction To Ambient	R_{thJA}	417	°C/W
Operation Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	°C

SS8050

CLASSIFICATION OF h_{FE1}

Rank	L	H	J
Range	120-200	200-350	300-400

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100\mu\text{A}$, $I_E = 0$	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 0.1\text{ mA}$, $I_B = 0$	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100\mu\text{A}$, $I_C = 0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB} = 40\text{V}$, $I_E = 0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = 20\text{V}$, $I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5\text{V}$, $I_C = 0$			0.1	μA
DC current gain	h_{FE1}	$V_{CE} = 1\text{V}$, $I_C = 100\text{mA}$	120		400	
	h_{FE2}	$V_{CE} = 1\text{V}$, $I_C = 800\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 800\text{mA}$, $I_B = 80\text{mA}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 800\text{mA}$, $I_B = 80\text{mA}$			1.2	V
Transition frequency	f_T	$V_{CE} = 10\text{V}$, $I_C = 50\text{mA}$, $f = 30\text{MHz}$	100			MHz

RATING AND CHARACTERISTIC CURVES (SS8050)

